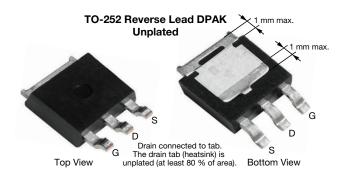


Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0087				
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0106				
I _D (A)	86				
Configuration	Single				
Package	TO-252 Reverse Lead DPAK				

FEATURES

- TrenchFET® power MOSFET
- Unplated drain tab (heatsink)
- Package with low thermal resistance
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



G O	
N-Channel MOSFET	o _e

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	100	.,	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C	1	86		
Continuous Drain Current	T _C = 125 °C	l _D	50		
Continuous Source Current (Diode conduction) a		Is	100	Α	
Pulsed Drain Current ^b		I _{DM}	150		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	45		
Single Pulse Avalanche Energy	L=U.I IIII	E _{AS}	101	mJ	
Maximum Power Dissipation b	T _C = 25 °C	P _D	136	W	
iviaximum rower bissipation -	T _C = 125 °C		45		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB mount c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.1	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					•	l	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 100 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
		V _{GS} = 10 V	I _D = 25 A	-	0.0072	0.0087	
Drain-Source On-State Resistance a	В	V _{GS} = 4.5 V	I _D = 20 A	-	0.0087	0.0106	
Diani-Source On-State nesistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 25 A, T _J = 125 °C	-	-	0.0144	Ω
		V _{GS} = 10 V	I _D = 25 A, T _J = 175 °C	-	-	0.0177	
Forward Transconductance b	9 _{fs}	V _{DS}	V _{DS} = 15 V, I _D = 25 A		80	=	S
Dynamic ^b	•	·					
Input Capacitance	C _{iss}			-	2550	3500	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	1350	1900	pF
Reverse Transfer Capacitance	C _{rss}]		-	101	140	1
Total Gate Charge ^c	Qg			-	42	65	
Gate-Source Charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_{D} = 50 \text{ A}$	-	7	-	nC
Gate-Drain Charge ^c	Q _{gd}]		-	8	=	
Gate Resistance	Rg	f = 1 MHz		1.4	2.9	4.4	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	12	20	
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, \text{ R}_{L} = 1 \Omega$ $I_{D} \cong 50 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	5	10	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	35	60	
Fall Time ^c	t _f			-	6	15	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	150	Α
Forward Voltage	V _{SD}	I _F =	25 A, V _{GS} = 0 V	-	0.88	1.5	V
	•	•				•	•

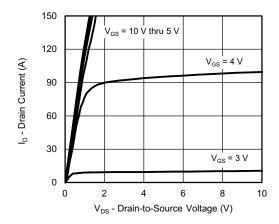
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

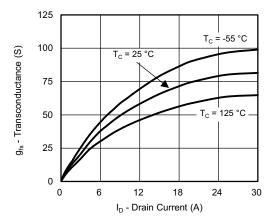
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



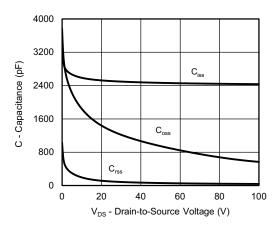
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



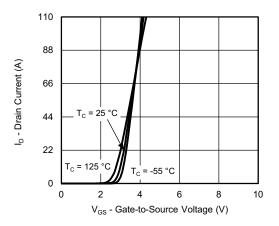
Output Characteristics



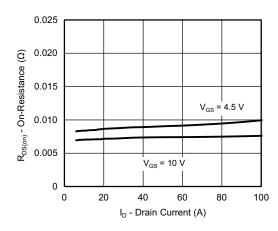
Transconductance



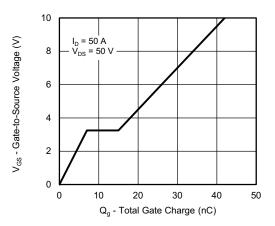
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current

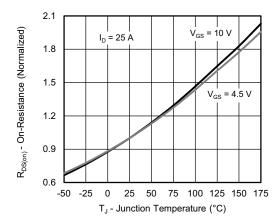


Gate Charge

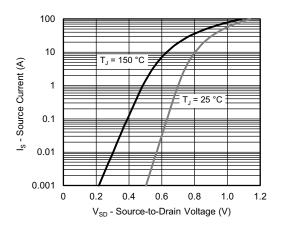
For technical questions, contact: automostechsu



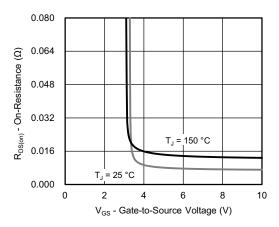
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



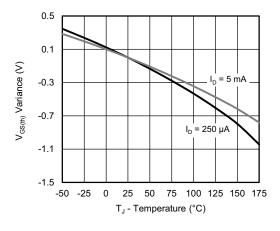
On-Resistance vs. Junction Temperature



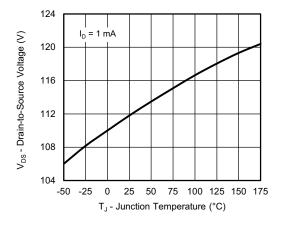
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



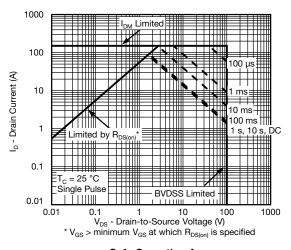
Threshold Voltage



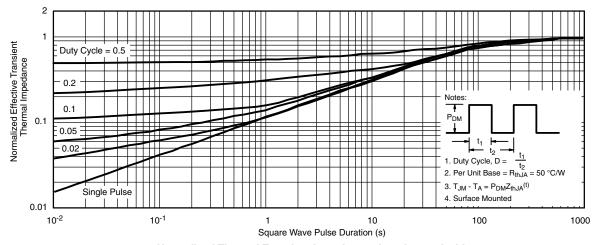
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



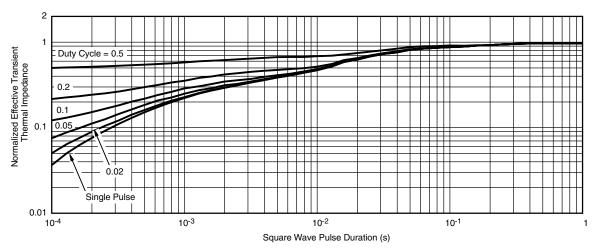
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

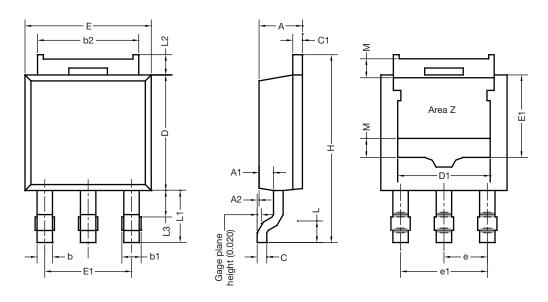
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75462.

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TO-252 Reverse Lead Case Outline



Notes

- Dimension L3 for reference only
- Area Z: unplated area more than 80 % heatsink area and for partial plating part only

DIM.	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
Α	2.23	2.33	0.088	0.092
A1	0.64	0.89	0.025	0.035
A2	0.03	0.18	0.001	0.007
b	0.71	0.88	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.44	0.206	0.214
С	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.49	5.00	0.177	0.197
E	6.48	6.73	0.255	0.265
E1	4.32	-	0.170	-
е	2.2	2.28 BSC		090 BSC
e1	4.5	57 BSC	0.1	180 BSC
Н	9.65	10.41	0.380	0.410
L	1.40	1.78	0.055	0.070
L1	2.74 BSC		0.1	108 BSC
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.040	0.060
М	-	1.00 (reference only)	-	0.039 (reference only

ECN: T16-0952-Rev. D, 16-Jan-17

DWG: 5894



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